

/ Descriptions

TO-251 M M E N 3 MOS 3 6 2 1
N-CHANNEL MOSFET in a TO-251 Plastic Package.

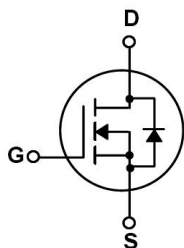
/ Features

U_{GS} 10V, r_{DS(on)} 1.5Ω, Q_g 10nC
Low gate charge, low crss, fast switching.

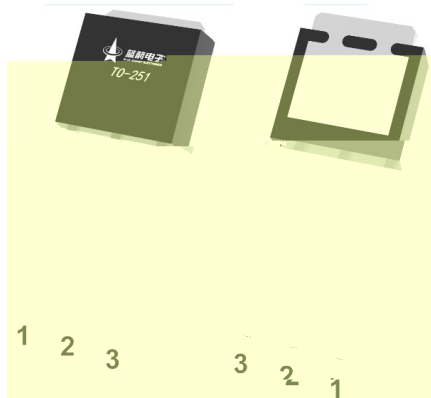
/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 X G

PIN 2 X D

PIN 3 X S

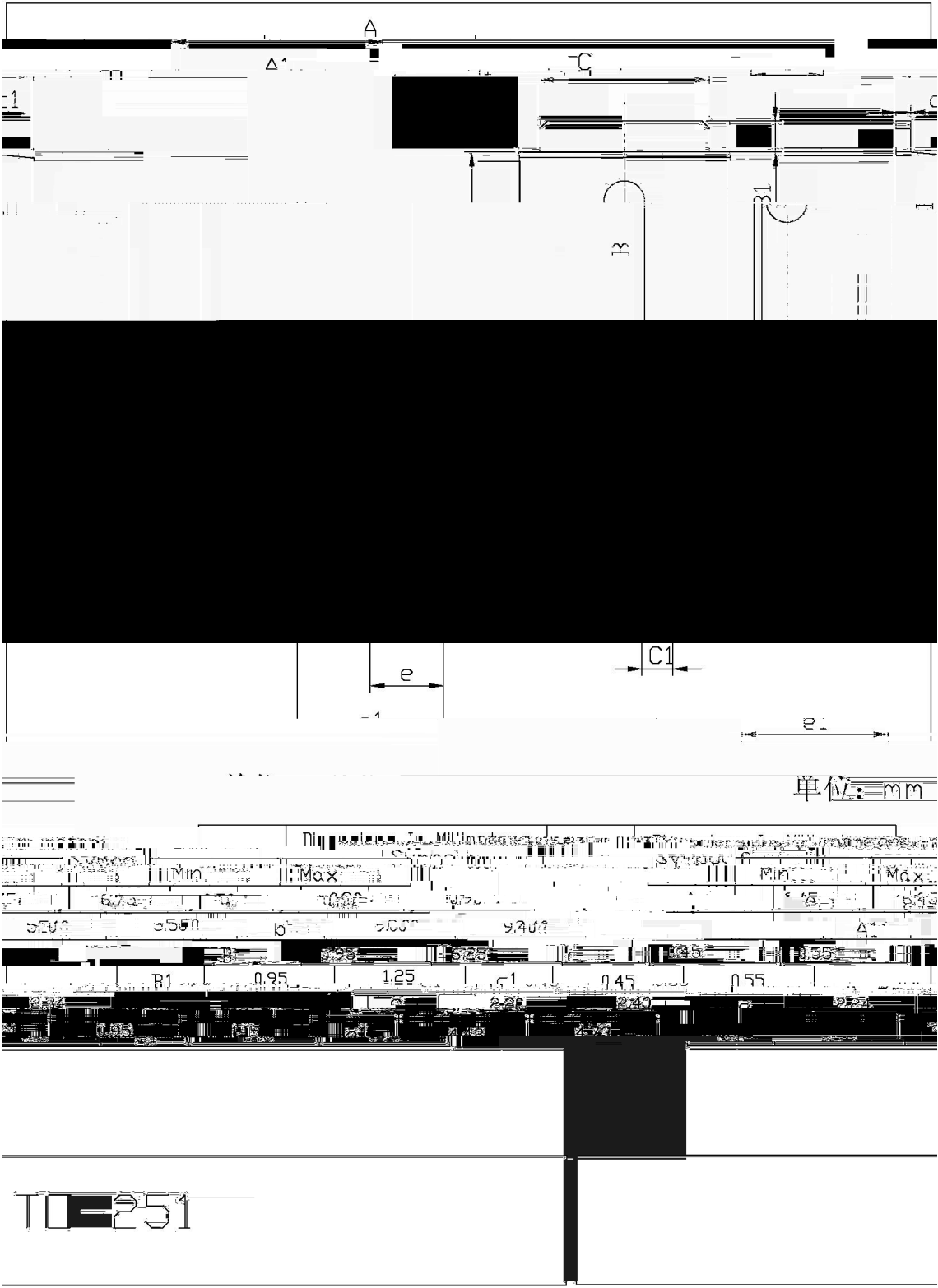
/ Marking

See Marking Instructions.

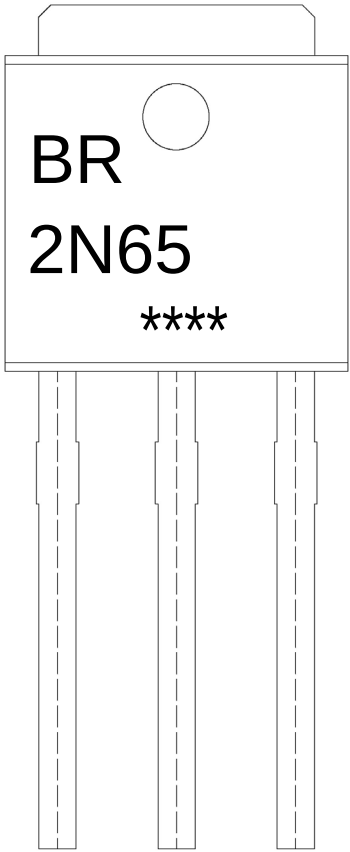
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	2.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	1.3	A
Drain Current - Pulsed	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	120	mJ
Repetitive Avalanche Energy	E_{AR}	5.4	mJ
Avalanche Current	I_{AR}	2.0	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	28	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	110	$^\circ\text{C/W}$
Junction to Case	$R_{\theta JC}$	4.46	$^\circ\text{C/W}$

BRI2N65

/ Package Dimensions



/ Marking Instructions



公司代码	公司代码
BR	公司代码
5Q98	公司代码
----	公司代码 1 2 3 4 5 6 7 8 9 10
Note:	
BR:	Company Code
2N65:	Product Type
****:	Lot No. Code, code change with Lot No

